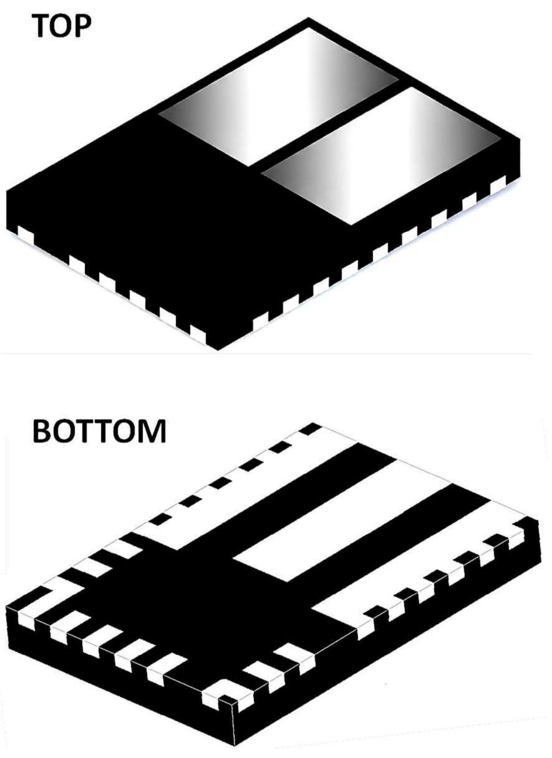
GR-10Z011FQ: 100V High-low Side GaN with Integrated Driver

Description

The GR-10Y005ZQ is a Gallium Nitride (GaN) FET with integrated driver. The device features High-side and low-side 100V rated GaN FET driven by an optimized high-frequency GaN FET driver. The GR-10Z011FQ incorporates an high-side level shifter and bootstrap circuit. This integration allows GR-10Z011FQ unit to form a half-bridge topology without the need for external level-shifting circuit. The driver and the GaN FET are mounted using Flip-chip bond packaging technology, resulting in minimized package parasitic elements.

GR-10Z011FQ (Dual-Side Cooling)



Key Specifications

Part Number	GR-10Z011ZQ
V_{DSS}, min.	100V
$R_{DS(ON)}$, typ.	11mΩ (HS & LS FET)
Package	QFN-3.5 x 5.0

Features

- Gate drive voltage compatibility
- High operating frequency
- Over temperature protection
- Short circuit protection
- 20 ns typical delay time

Applications

- Buck, boost, buck-boost converters
- AC-DC/ DC-DC Converters
- Motor Drives